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6/20/03
506.36904X00
C. Moore

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: MIURA, et al.
Serial No.: 09/254,939
Filed: March 17, 1999
For: METHOD OF FABRICATING SEMICONDUCTOR DEVICE
HAVING TRENCH ELEMENT SEPARATION STRUCTURE
Group: 2814
Examiner: Anh D. Mai

AMENDMENT

Mail Stop
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

June 5, 2003

Sir:

In response to the Office Action mailed March 5, 2003, please amend the
above-identified application as follows:

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IN THE CLAIMS

Please amend the claims presently in the application as follows:

1. (Five Times Amended) A method of fabricating a semiconductor
device comprising the steps of:
- (a) forming an oxidation prevention film on a circuit formation surface of a
semiconductor substrate;
 - (b) forming a trench having a desired depth at a predetermined position of

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01 FC:1201
02 FC:1202

84.00 OP
18.00 OP